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| **Exhibitor Introduction (Within 200 words)** | Customers in the high-technology fields of semiconductor, display, and nano technologies have required the ceaseless R & D of equipment and process. Accordingly, CN1, as a strong leader in the field of ALD, has continued technical development and innovation to quickly respond to such needs.<br>The ALD systems made by CN1 are widely used in hundreds of universities, National Institutes, and enterprises in Korea. Furthermore, CN1's ALD business is globally expanded into U.S.A., Japan, Singapore, Taiwan, Russia, and China. The supplied ALD systems by CN1 are firmly recognized by renowned universities and companies. CN1, named from "Can Be the Number One," is doing its best to grow into a globally reliable business, based on the innovativeness of the ALD technology. |
| **Exhibit Description (Within 200 words)** | **1. Atomic-Premium**<br>**Showerhead type Plasma-Enhanced ALD (PE-ALD)**<br>• Plasma process & treatment<br>• Adjustable the gap between showerhead and substrate<br>• Variable gas delivery system : Bubbler, Vaporizer, LDS<br>• Completely separated source delivery<br>• Configuration ALD/CVD mode process<br>• Good film uniformity & quality<br>• Process temperature : up to 500°C<br>• Precursor canister : 4EA(standard)<br>• Substrate Size : 4 ~ 12" wafer<br>• Applications<br>Dielectric thin films : $Al_2O_3$, $HfO_2$, $ZrO_2$, $TiO_2$, $ZnO_2$, ZnS, GST, Laminate films, etc.<br>Nitride films :AlN, TiN, TiAlN, TaN, etc. |

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| | Metal films :Ru, Co, Ti, Ni, etc.<br>**2. Atomic-Classic**<br>**Traveling wave type ALD**<br>• Traveling wave type thermal ALD<br>• Laminar gas flow (Side gas flow)<br>• Variable gas delivery system : Bubbler, LDS<br>• Low particle generation<br>• Very small volume for process<br>• Available laminated & mixed process<br>• Process temperature : up to 450°C<br>• Precursor canister : 4EA(standard)<br>• Substrate size :<br>4 ~ 8” wafer<br>2G : 370x470mm glass<br>• Applications<br>Dielectric thin films : Al2O3, HfO2, ZrO2, TiO2, ZnO2, STO, ZnS, Laminate films, etc.<br>**3. Atomic-Shell**<br>**Rotating reactor ALD for shell coating on core structure**<br>• Nano size powder coating system<br>• Reactor volume : > 100cc<br>• Filter size : Variable (from 0.5μm~)<br>• Horizontal rotation system<br>• Precursor canister : 4EA<br>• Process temperature : R.T. ~ 350°C (Reactor body : 230°C)<br>• Reactor rotation : DC Motor<br>• Rotation speed : 10 ~ 120rpm<br>• Base pressure : under 20mTorr<br>• Applications : Coating on particle, wire, tube, etc. |
| **Exhibit Product** | 1. Posters : ALD Systems (Atomic Premium, Atomic Classic, Atomic Shell)<br>2. Canister for ALD, CVD |